

I-Chung Chiu

List of Publications by Year in descending order

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Version: 2024-02-01

12
papers

204
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1478505

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12
times ranked

258
citing authors

#	ARTICLE	IF	CITATIONS
1	Gate-Bias Stress Stability of P-Type SnO Thin-Film Transistors Fabricated by RF-Sputtering. IEEE Electron Device Letters, 2014, 35, 90-92.	3.9	63
2	Complementary Oxide-Semiconductor-Based Circuits With n-Channel ZnO and p-Channel SnO Thin-Film Transistors. IEEE Electron Device Letters, 2014, 35, 1263-1265.	3.9	59
3	Influence of rapid-thermal-annealing temperature on properties of rf-sputtered SnO _x thin films. Applied Surface Science, 2015, 327, 358-363.	6.1	27
4	Flexible Transparent ZnO:Al/ZnO/CuAlO _x :Ca Heterojunction Diodes on Polyethylene Terephthalate Substrates. Journal of Electronic Materials, 2013, 42, 1242-1245.	2.2	24
5	Two dimensional thermoelectric platforms for thermocapillary droplet actuation. RSC Advances, 2012, 2, 1639-1642.	3.6	11
6	Optoelectronic properties of infrared rapid-thermal-annealed SnO _x thin films. Ceramics International, 2015, 41, 13502-13508.	4.8	8
7	Nitrogen Atmospheric-Pressure-Plasma-Jet Induced Oxidation of SnO _x Thin Films. Plasma Chemistry and Plasma Processing, 2015, 35, 979-991.	2.4	5
8	Electromechanical Stability of Flexible Nanocrystalline-Silicon Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 222-224.	3.9	4
9	Oxidation of sputtered metallic Sn thin films using N ₂ atmospheric pressure plasma jets. Materials Research Express, 2015, 2, 016504.	1.6	2
10	Effects of electro-mechanical stressing on the electrical characterization of on-plastic a-Si:H thin film transistors. Materials Research Society Symposia Proceedings, 2009, 1153, 1.	0.1	1
11	DC and AC Gate-Bias Stability of Nanocrystalline Silicon Thin-Film Transistors Made on Colorless Polyimide Foil Substrates. Materials Research Society Symposia Proceedings, 2011, 1321, 259.	0.1	0
12	Enhancement of gate-bias and current stress stability of P-type SnO thin-film transistors with SiN _x /HfO ₂ passivation layers. , 2016, , .		0